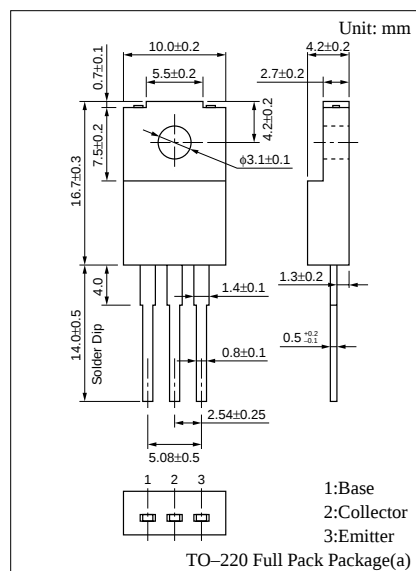


Silicon NPN triple diffusion planar type Darlington

Complementary to 2SB1252

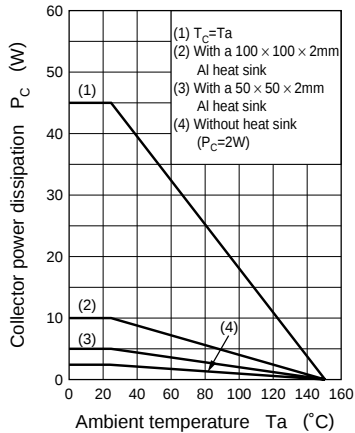
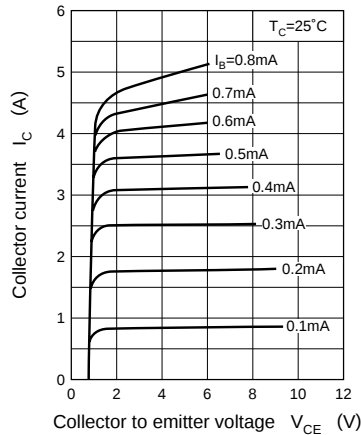
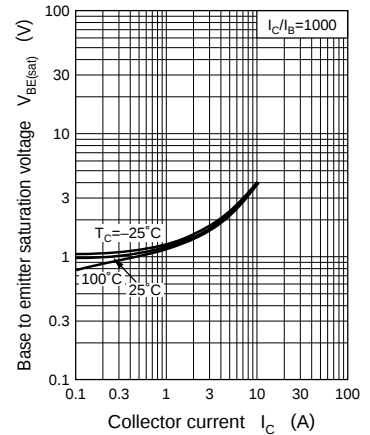
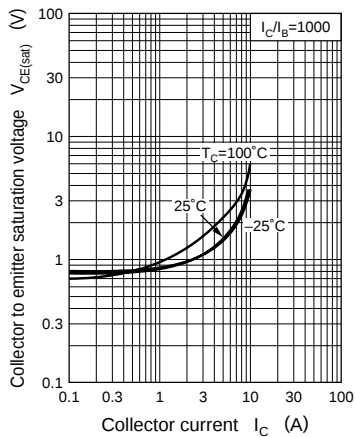
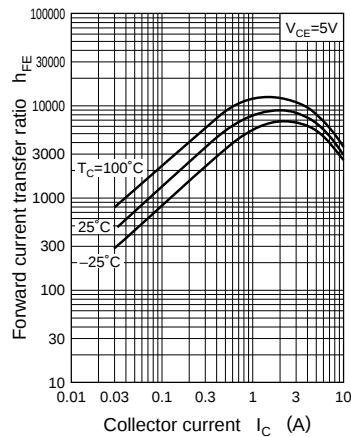
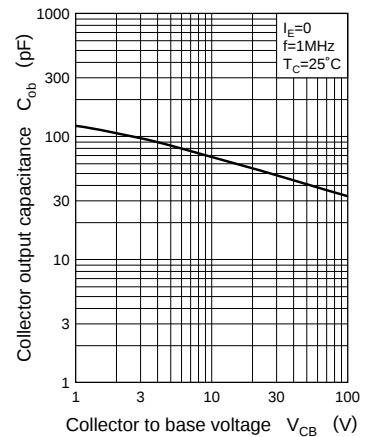
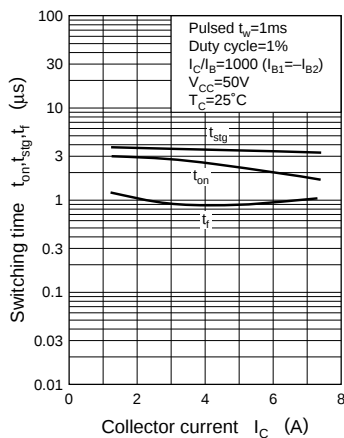
- Optimum for 35W HiFi output
- High forward current transfer ratio h_{FE} : 5000 to 30000
- Low collector to emitter saturation voltage $V_{CE(sat)}$: <2.5V
- Full-pack package which can be installed to the heat sink with one screw

Parameter		Symbol	Ratings	Unit
Collector to base voltage		V_{CBO}	120	V
Collector to emitter voltage		V_{CEO}	100	V
Emitter to base voltage		V_{EBO}	5	V
Peak collector current		I_{CP}	8	A
Collector current		I_C	5	A
Collector power dissipation	$T_C=25^{\circ}\text{C}$	P_C	45	W
	$T_a=25^{\circ}\text{C}$		2	
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature		T_{stg}	-55 to +150	$^{\circ}\text{C}$



Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 120V, I_E = 0$			100	μA
	I_{CEO}	$V_{CE} = 100V, I_B = 0$			100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			100	μA
Collector to emitter voltage	V_{CEO}	$I_C = 30mA, I_B = 0$	100			V
Forward current transfer ratio	h_{FE1}	$V_{CE} = 5V, I_C = 1A$	2000			
	h_{FE2}^*	$V_{CE} = 5V, I_C = 4A$	5000		30000	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 4A, I_B = 4mA$			2.5	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 4A, I_B = 4mA$			3.0	V
Transition frequency	f_T	$V_{CE} = 10V, I_C = 0.5A, f = 1MHz$		20		MHz
Turn-on time	t_{on}	$I_C = 4A, I_{B1} = 4mA, I_{B2} = -4mA,$ $V_{CC} = 50V$		2.5		μs
Storage time	t_{stg}			3.5		μs
Fall time	t_f			1.0		μs

Rank	Q	P
h _{FE2}	5000 to 15000	8000 to 30000

$P_C - T_a$  $I_C - V_{CE}$  $V_{BE(sat)} - I_C$  $V_{CE(sat)} - I_C$  $h_{FE} - I_C$  $C_{ob} - V_{CB}$  $t_{on}, t_{stg}, t_f - I_C$ 

Area of safe operation (ASO)

